



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
PNP SILICON Transistor**

VOLTAGE 300 Volts CURRENT 0.5 Ampere

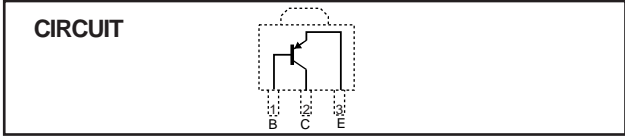
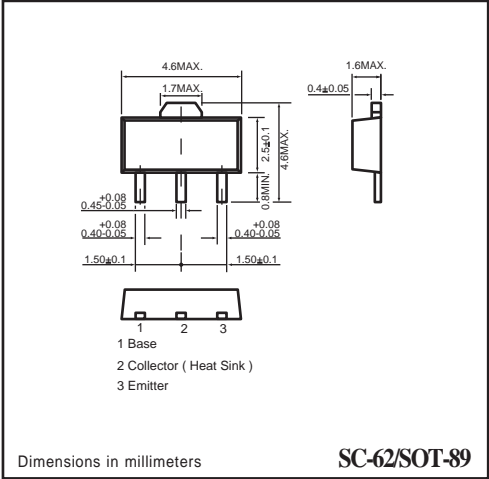
CHTA92XGP

APPLICATION
* Telephony and professional communication equipment.
* Other switching applications.

FEATURE
* Suitable for high packing density.

CONSTRUCTION
*PNP SILICON Transistor

MARKING
*ZFP



LIMITING VALUES
In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	—	-300	V
V _{CEO}	collector-emitter voltage	open base	—	-300	V
V _{EBO}	emitter-base voltage	open collector	—	-5	V
I _C	collector current (DC)		—	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	—	1200	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		—	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note
1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHTA92XGP)

THEMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	104	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$V_{CB} = -200\text{ V}$	–	-250	nA
I_{EBO}	emitter cut-off current	$V_{EB} = -3.0\text{ V}$	–	-100	nA
h_{FE}	DC current gain	$I_C = -1\text{ mA}; V_{CE} = -10\text{ V}$ $I_C = -10\text{ mA}; V_{CE} = -10\text{ V}$ $I_C = -30\text{ mA}; V_{CE} = -10\text{ V}$	25 40 40	–	–
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = -20\text{ mA}, I_B = -2.0\text{ mA}$	–	-0.5	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C = -20\text{ mA}, I_B = -2.0\text{ mA}$	–	-0.9	V
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = -20\text{ V};$ $f = 100\text{ MHz}$	50	–	
C_{ob}	collector capacitance	$V_{CB} = 20\text{ V}, I_E = 0, f = 1.0\text{ MHz}$	–	6.0	pF